

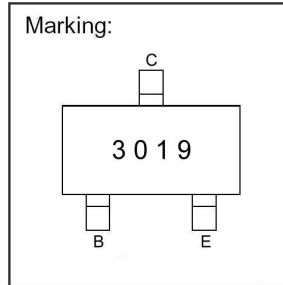
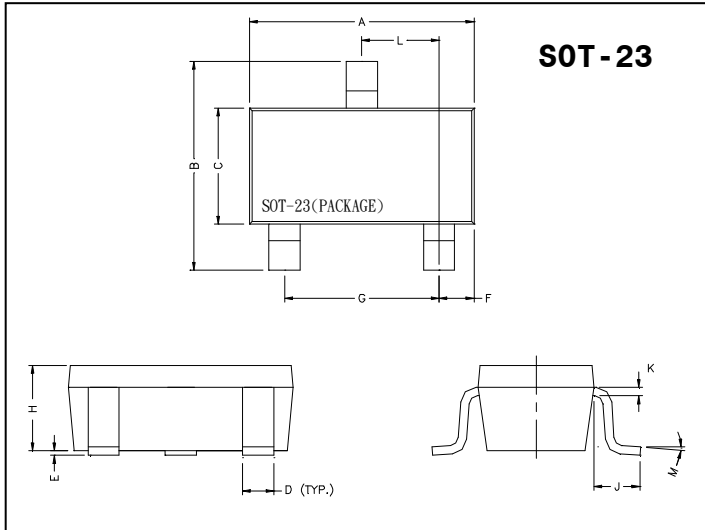
GMBT3019

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT3019 is designed for general purpose amplifier applications and switching requiring collector currents 1A.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	140	V
Collector to Emitter Voltage	VCEO	80	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	1	A
Total Power Dissipation	PD	350	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	140	-	-	V	IC=100uA
BVCEO	80	-	-	V	IC=30mA
BVEBO	7	-	-	V	IE=100uA
ICBO	-	-	50	nA	VCB=90V
IEBO	-	-	50	nA	VEB=5V
VCE(sat)	-	-	0.2	V	IC=150mA, IB=15mA
VBE(sat)	-	-	1.1	V	IC=150mA, IB=15mA
hFE1	50	-	-		VCE=10V, IC=0.1mA
hFE2	90	-	-		VCE=10V, IC=10mA
hFE3	100	-	300		VCE=10V, IC=150mA
hFE4	50	-	-		VCE=10V, IC=500mA
hFE5	15	-	-		VCE=10V, IC=1000mA
fT	100	-	-	MHz	VCE=50mV, IC=50mA, f=100MHz
Cob	-	-	12	pF	VCE=10V, IE=0, f=1MHz

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